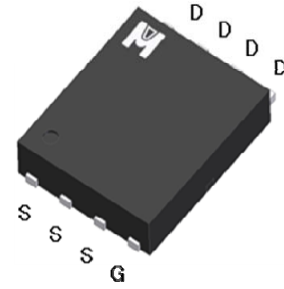


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

$BV_{DSS}$	60V
$R_{DS(on) (MAX.)}$	6m $\Omega$
$I_D$	68A



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	$I_D$	68	A
	$T_C = 100^\circ\text{C}$		40	
Pulsed Drain Current <sup>1,3</sup>		$I_{DM}$	170	
Avalanche Current		$I_{AS}$	68	
Avalanche Energy	$L = 0.1\text{mH}, I_D=68\text{A}, R_G=25\Omega$	$E_{AS}$	230	mJ
Repetitive Avalanche Energy <sup>2</sup>	$L = 0.05\text{mH}$	$E_{AR}$	115	
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	50	W
	$T_C = 100^\circ\text{C}$		20	
Operating Junction & Storage Temperature Range		$T_{j}, T_{stg}$	-55 to 150	$^\circ\text{C}$

100% UIS testing in condition of  $V_D=30\text{V}, L=0.1\text{mH}, V_G=10\text{V}, I_L=25\text{A}$ , Rated  $V_{DS}=60\text{V}$  N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		2.5	$^\circ\text{C} / \text{W}$
Junction-to-Ambient <sup>4</sup>	$R_{\theta JA}$		50	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle  $\leq 1\%$

<sup>3</sup>Pulsed drain current rating is package limited.

<sup>4</sup>50 $^\circ\text{C} / \text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125 °C			25	
On-State Drain Current <sup>1</sup>	I <sub>D(ON)</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 10V	68			A
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A		5.0	6.0	mΩ
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 30A		52		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz		3057		pF
Output Capacitance	C <sub>oss</sub>			441		
Reverse Transfer Capacitance	C <sub>rss</sub>			112		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 15mV, V <sub>DS</sub> = 0V, f = 1MHz		2.7		Ω
Total Gate Charge <sup>1,2</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A		40		nC
Gate-Source Charge <sup>1,2</sup>	Q <sub>gs</sub>			17		
Gate-Drain Charge <sup>1,2</sup>	Q <sub>gd</sub>			11		
Turn-On Delay Time <sup>1,2</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = 30V, I <sub>D</sub> = 1A, V <sub>GS</sub> = 10V, R <sub>GS</sub> = 6Ω		20		nS
Rise Time <sup>1,2</sup>	t <sub>r</sub>			75		
Turn-Off Delay Time <sup>1,2</sup>	t <sub>d(off)</sub>			110		
Fall Time <sup>1,2</sup>	t <sub>f</sub>			85		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>C</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>				68	A
Pulsed Current <sup>3</sup>	I <sub>SM</sub>				170	
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = 20A, V <sub>GS</sub> = 0V			1.3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 25A, dI <sub>F</sub> /dt = 100A / μS		35		nS
Reverse Recovery Charge	Q <sub>rr</sub>				160	

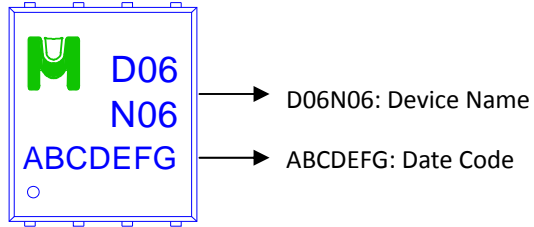
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Pulse width limited by maximum junction temperature.

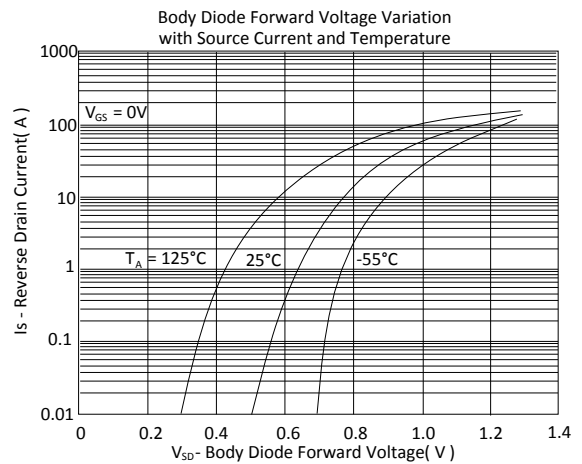
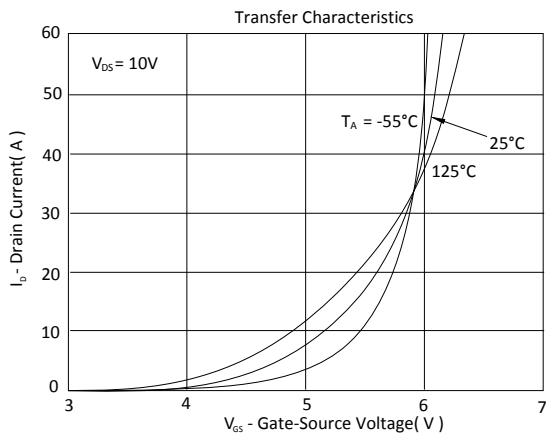
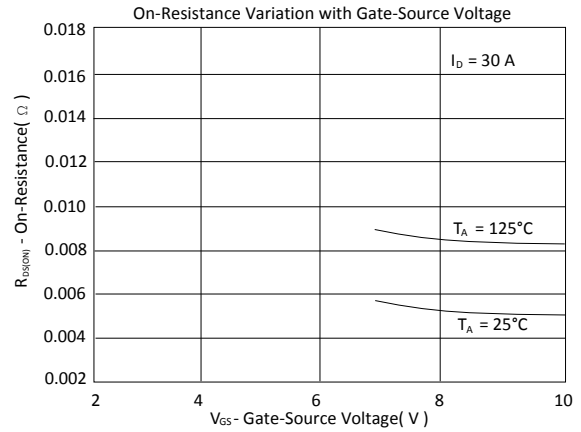
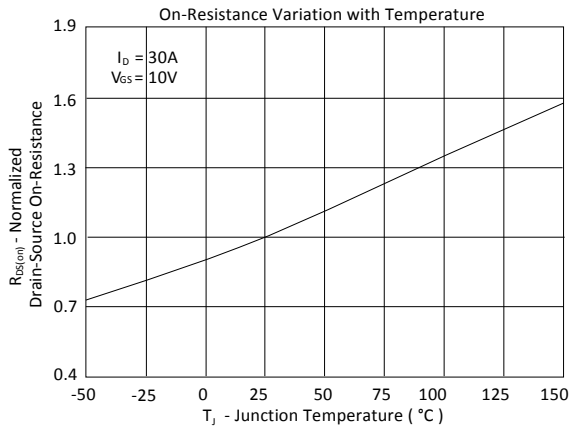
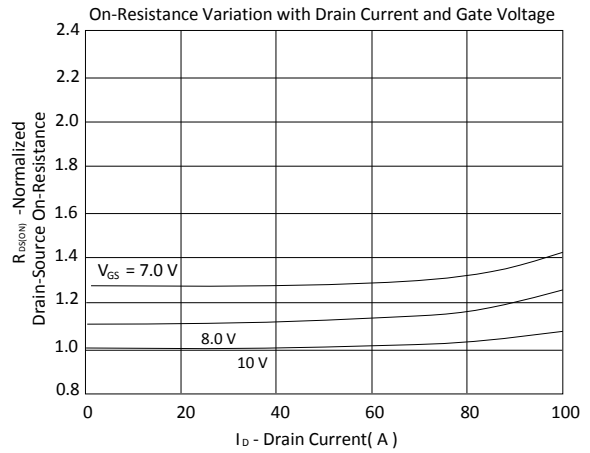
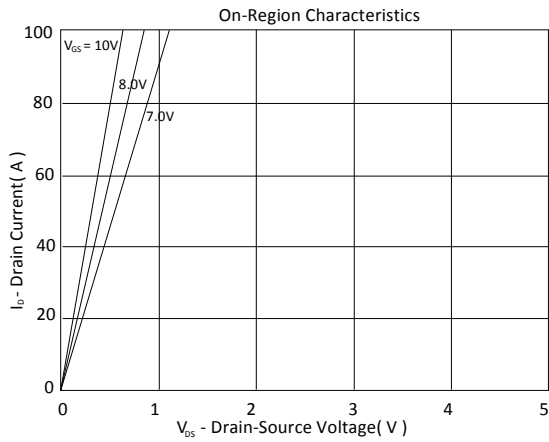
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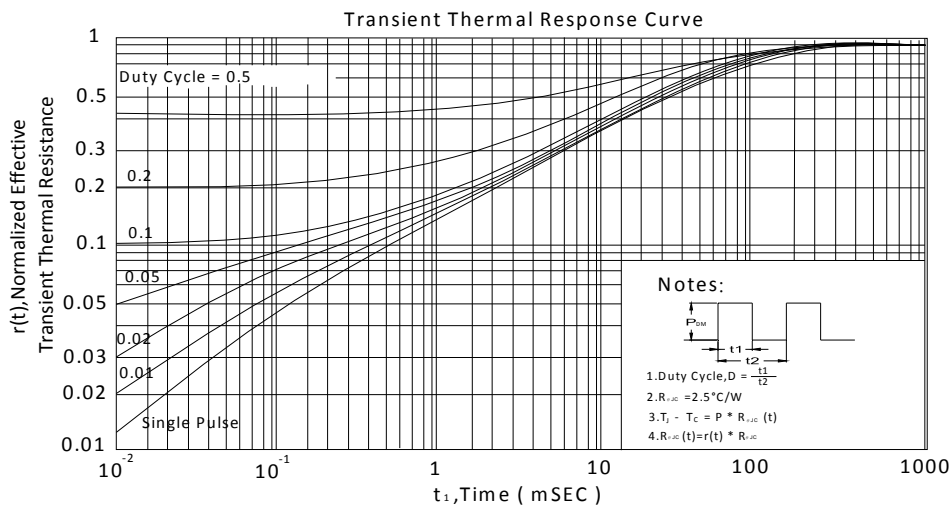
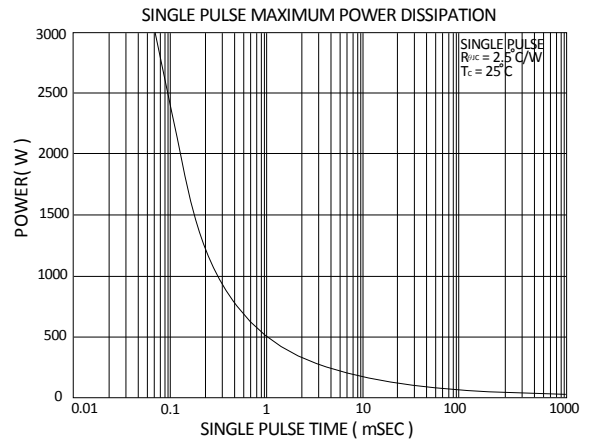
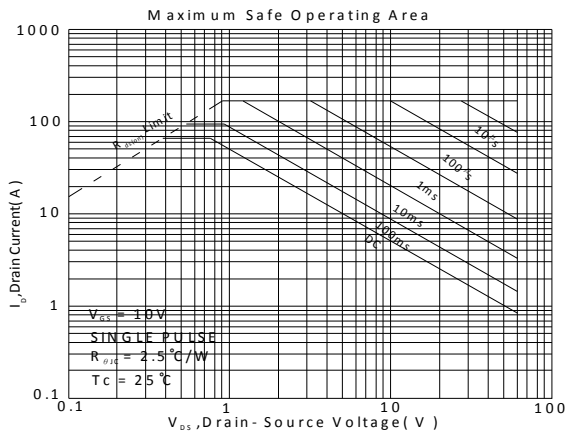
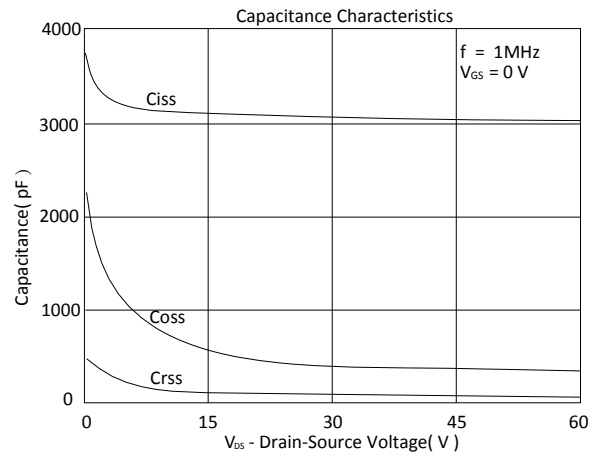
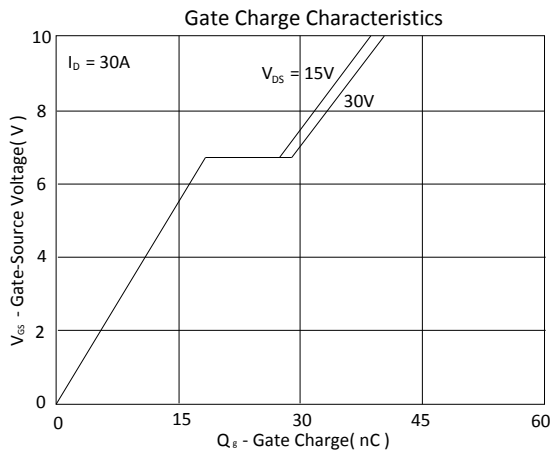
Device Name: EMD06N06H for EDFN 5 x 6





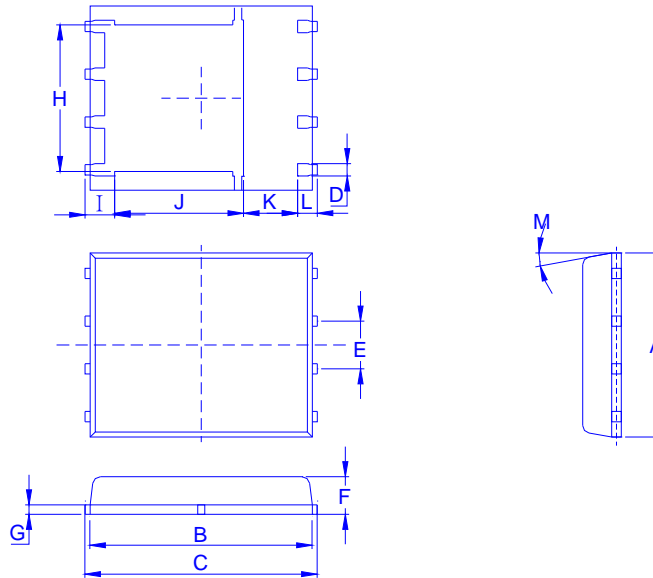
TYPICAL CHARACTERISTICS







Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K	L	M
Min.	4.80	5.50	5.90	0.3		0.85	0.15	3.67	0.41	3.00	0.94	0.45	0°
Typ.					1.27								
Max.	5.30	5.90	6.15	0.51		1.20	0.30	4.54	0.85	3.92	1.7	0.71	12°

Recommended minimum pads

